

ABSTRACT

A gate driver for forcing a power transistor including a gate electrode insulated with oxide film into conduction or shut-off, the gate driver includes a first current source for outputting a first current value to raise an electric potential of the gate electrode for changing shut-off state of the power transistor to conductive state; and a second current source for outputting a second current value to lower the electric potential of the gate electrode for changing the conductive state of the power transistor to the shut-off state. The first current value and the second current value are assigned based on at least one kind of current source control information. This structure allows preparing an appropriate speed of forcing the power transistor into conduction or shut-off with a small number of elements, and the gate driver can be used with ease for driving power transistors having different output sizes.